

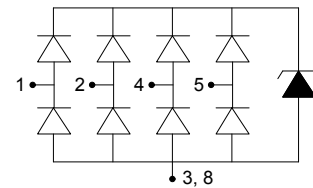
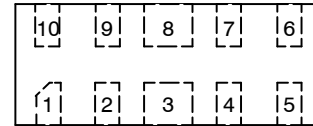
The ESD7504 surge protection is designed to protect high speed data lines from ESD. Ultra-low capacitance and low ESD clamping voltage make this device an ideal solution for protecting voltage sensitive high speed data lines. The flow-through style package allows for easy PCB layout and matched trace lengths necessary to maintain consistent impedance between high speed differential lines such as USB 3.0.

Features

- Low Capacitance (0.55 pF Max, I/O to GND)
- Protection for the Following IEC Standards:
IEC 61000-4-2 (Level 4)
- Low ESD Clamping Voltage
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- USB 3.0
- eSATA 1.0/2.0/3.0
- HDMI 1.3/1.4
- Display Port



Pin	Name	Description
1	IO	Connect to IO
2	IO	Connect to IO
3	GND	Connect to GND
4	IO	Connect to IO
5	IO	Connect to IO
6	NC	NO Connection
7	NC	NO Connection
8	GND	Connect to GND
9	NC	NO Connection
10	NC	NO Connection

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Operating Junction Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Seconds)	T _L	260	°C
IEC 61000-4-2 Contact (ESD)	ESD	±15	kV
IEC 61000-4-2 Air (ESD)	ESD	±15	kV

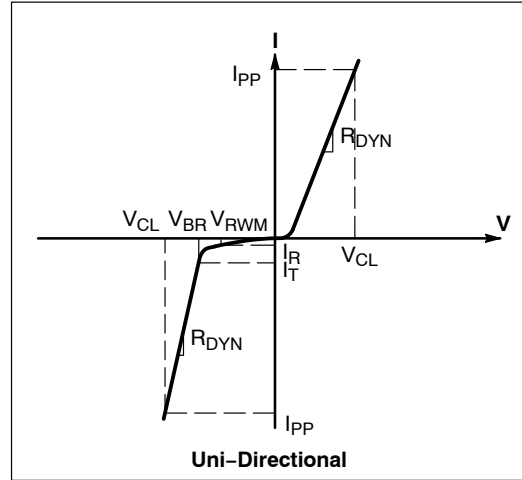
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
I _{PP}	Maximum Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
R _{DYN}	Dynamic Resistance

*See Application Note AND8308/D for detailed explanations of datasheet parameters.



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Working Voltage	V _{RWM}	I/O Pin to GND			3.3	V
Breakdown Voltage	V _{BR}	I _T = 1 mA, I/O Pin to GND	4.0	5.0		V
Reverse Leakage Current	I _R	V _{RWM} = 3.3 V, I/O Pin to GND			1.0	μA
Clamping Voltage (Note 1)	V _C	IEC61000-4-2, ±8 kV Contact	See Figures 1 and 2			V
Clamping Voltage TLP (Note 2) See Figures 5 through 6	V _C	I _{PP} = 8 A I _{PP} = -8 A	IEC 61000-4-2 Level 2 equivalent (±4 kV Contact, ±4 kV Air)		10.2 -4.5	V
		I _{PP} = 16 A I _{PP} = -16 A	IEC 61000-4-2 Level 4 equivalent (±8 kV Contact, ±15 kV Air)		13.7 -8.1	
Junction Capacitance	C _J	V _R = 0 V, f = 1 MHz between I/O Pins and GND			0.55	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- For test procedure see Figures 3 and 4
- ANSI/ESD STM5.5.1 – Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model.
TLP conditions: Z₀ = 50 Ω, t_p = 100 ns, t_r = 4 ns, averaging window; t₁ = 30 ns to t₂ = 60 ns.

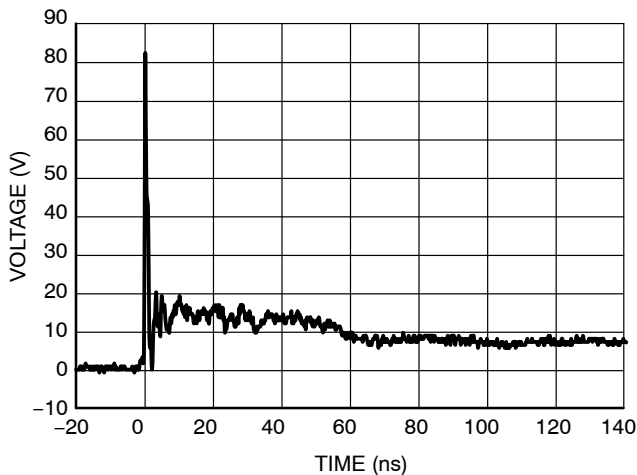


Figure 1. IEC61000-4-2 +8 kV Contact Clamping Voltage

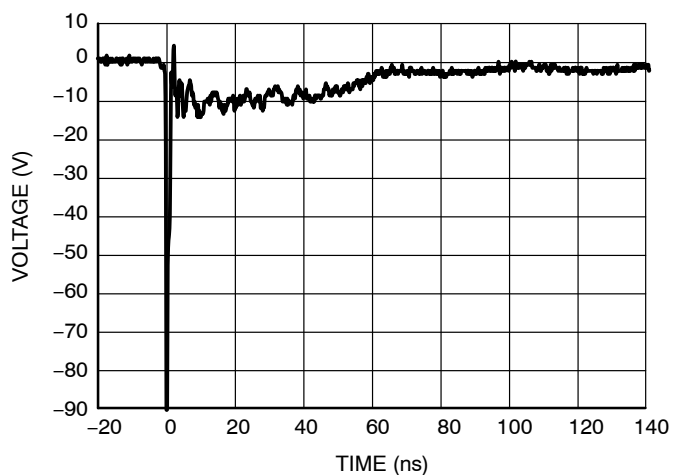


Figure 2. IEC61000-4-2 -8 kV Contact Clamping Voltage

IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

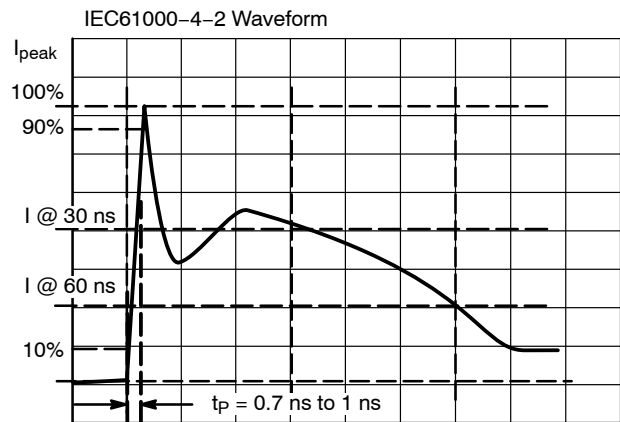


Figure 3. IEC61000-4-2 Spec

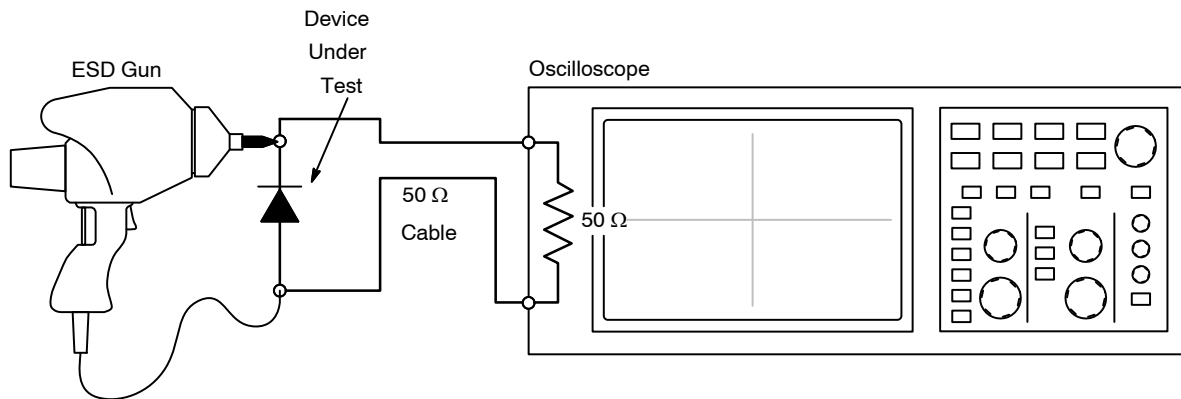
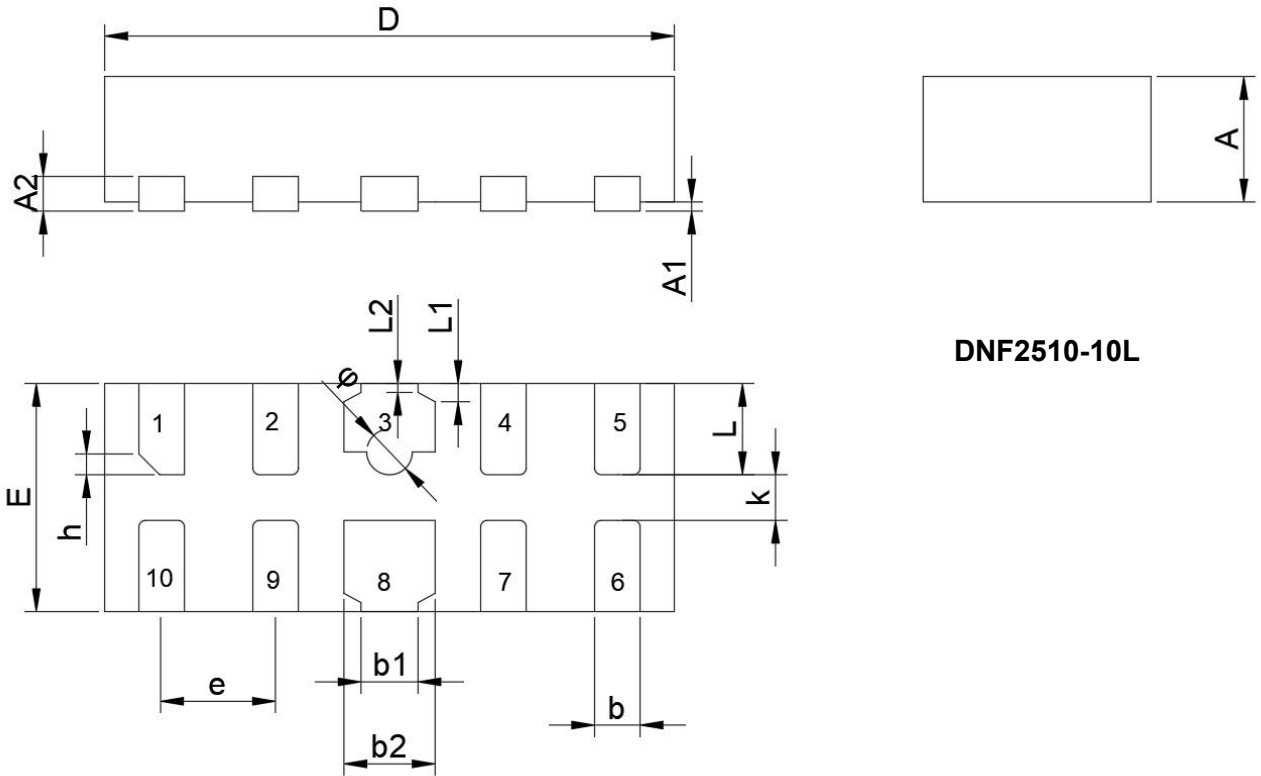


Figure 4. Diagram of ESD Clamping Voltage Test Setup

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for largesystems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. That has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes.

PACKAGE DIMENSIONS



DNF2510-10L

Dimensions in Millimeter							
Symbol	Min.	Nom.	Max.	Symbol	Min.	Nom.	Max.
A	0.500	0.550	0.600	D	2.450	2.500	2.550
A1	0.00	/	0.05	E	0.950	1.00	1.050
A2	0.122	0.152	0.200	e	0.450	0.500	0.550
b	0.150	0.200	0.250	h	0.080	0.120	0.150
b1	0.200	0.250	0.300	k	0.150	0.200	0.250
b2	0.350	0.400	0.450	L	0.350	0.400	0.450
L1		0.075		L2		0.05	
φ	0.150	0.200	0.250				

Table-5 Product dimensions

Ordering information

Order code	Package	Baseqty	Deliverymode
ESD7504MUTAG	DFN2510	3000	Tape and reel